SN74ACT151-Q1 Automotive 8-Line to 1-Line Data Selector/Multiplexer with TTL-Compatible Inputs

1 Features

- AEC-Q100 qualified for automotive applications:
  - Device temperature grade 1: -40°C to +125°C
  - Device HBM ESD classification level 2
  - Device CDM ESD classification level C4B
- Available in wettable flank QFN package
- Operating voltage range of 4.5V to 5.5V
- TTL-compatible inputs
- Continuous ±24mA output drive at 5V
- Supports up to ±75mA output drive at 5V in short bursts
- Drives 50Ω transmission lines
- Fast operation with delay of 16.9ns max

2 Applications

- Data selection
- Multiplexing

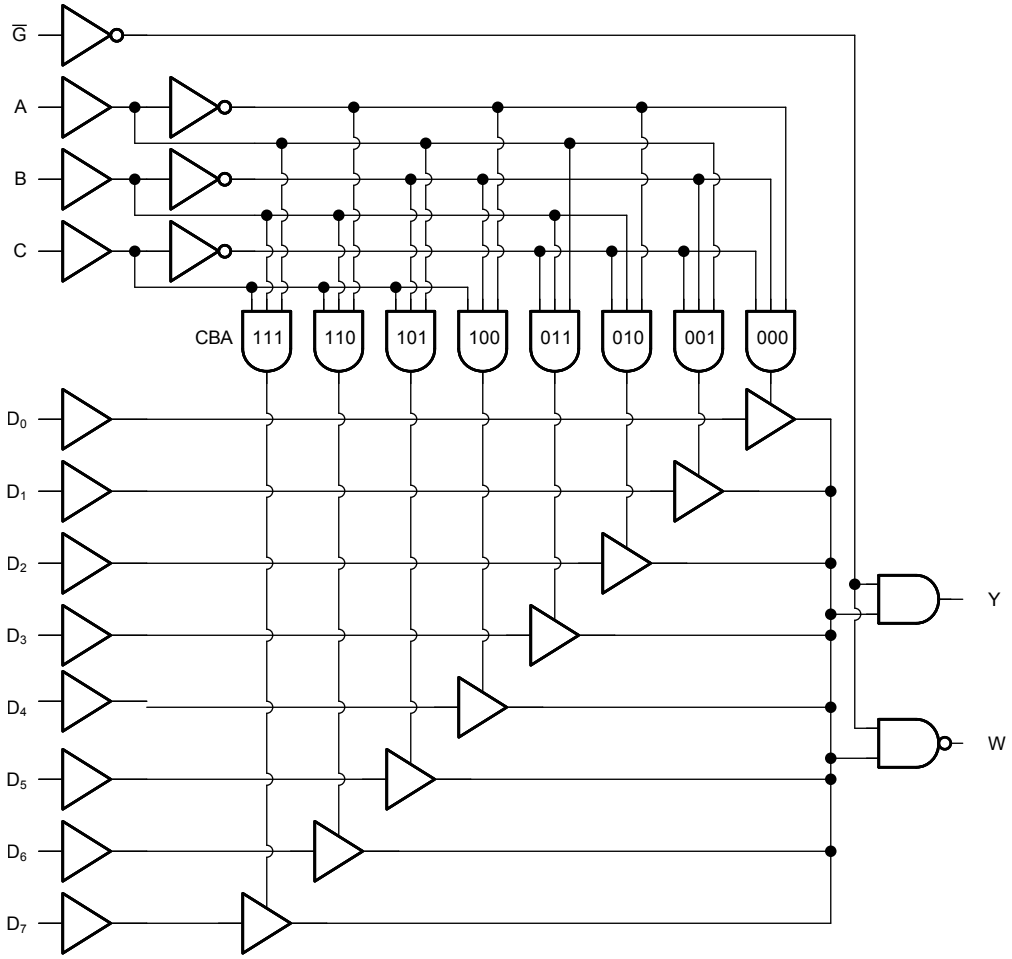
3 Description

The SN74ACT151-Q1 contains one 8 to 1 data selector/multiplexer with strobe ($\overline{G}$) input, standard output (Y), and inverted output (W).

Device Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)	BODY SIZE(3)
SN74ACT151-Q1	BQB (WQFN, 16)	3.5mm x 2.5mm	3.5mm x 2.5mm
	PW (TSSOP, 16)	5mm x 6.4mm	5mm x 4.4mm

(1) For more information, see Mechanical, Packaging, and Orderable InformationMechanical, Packaging, and Orderable Information.
(2) The package size (length × width) is a nominal value and includes pins, where applicable.
(3) The body size (length × width) is a nominal value and does not include pins.



Logic Diagram

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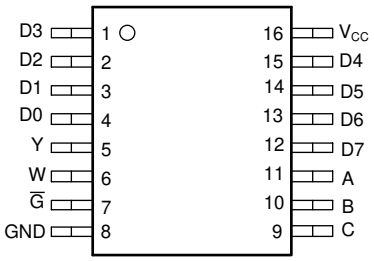
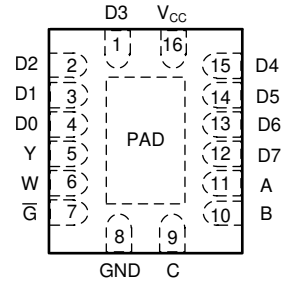
4 Pin Configuration and Functions



PW Package,
16-Pin TSSOP
(Top View)



BQB Package,
16-Pin WQFN
(Transparent Top View)

Table 4-1. Pin Functions

PIN		TYPE[2]	DESCRIPTION
NO.	NAME		
1	D3	I	Data input 3
2	D2	I	Data input 2
3	D1	I	Data input 1
4	D0	I	Data input 0
5	Y	O	Data output
6	W	O	Data output, inverted
7	$\overline{G}$	I	Output strobe, active low
8	GND	—	Ground
9	C	I	Address select C
10	B	I	Address select B
11	A	I	Address select A
12	D7	I	Data input 7
13	D6	I	Data input 6
14	D5	I	Data input 5
15	D4	I	Data input 4
16	V_{CC}	—	Positive supply
Thermal Pad [1]		—	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.

(1) BQB package only.
(2) Signal Types: I = Input, O = Output, I/O = Input or Output.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	7	V
V_I	Input voltage range(2)		-0.5	V_{CC} + 0.5	V
V_O	Output voltage range(2)		-0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < -0.5V or V_I > V_{CC} + 0.5V		±20	mA
I_{OK}	Output clamp current	V_O < -0.5V or V_O > V_{CC} + 0.5V		±50	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		±50	mA
	Continuous current through V_{CC} or GND			±200	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		-65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2(1)	±2000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	

(1) AEC Q100-002 indicate that HBM stressing shall be in accordrance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

Spec	Description	Condition	MIN	MAX	UNIT
V_{CC}	Supply voltage		4.5	5.5	V
V_{IH}	High-level input voltage		2		V
V_{IL}	Low-Level input voltage			0.8	V
V_I	Input Voltage		0	V_{CC}	V
V_O	Output Voltage		0	V_{CC}	V
I_{OH}	High-level output current			-24	mA
I_{OL}	Low-level output current			24	mA
Δt/Δv	Input transition rise or fall rate			20	ns/V
T_A	Operating free-air temperature		-40	125	°C

5.4 Thermal Information

PACKAGE	PINS	THERMAL METRIC(1)						UNIT
		$R_{\theta JA}$	$R_{\theta JC(top)}$	$R_{\theta JB}$	Ψ_{JT}	Ψ_{JB}	$R_{\theta JC(bot)}$	
PW (TSSOP)	16	139.5	74.8	97.7	17.8	96.6	N/A	°C/W

PACKAGE	PINS	THERMAL METRIC(1)						UNIT
		$R_{\theta JA}$	$R_{\theta JC(top)}$	$R_{\theta JB}$	Ψ_{JT}	Ψ_{JB}	$R_{\theta JC(bot)}$	
BQB (WQFN)	16	98.6	94.6	67.7	15.6	67.5	45.9	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	-40°C to 125°C			UNIT
			MIN	TYP	MAX	
V_{OH}	I_{OH} = -50µA	4.5V	4.4	4.499		V
		5.5V	5.4	5.499		
	I_{OH} = -24mA	4.5V	3.7	4.19		
	I_{OH} = -24mA	5.5V	4.7	5.22		
	I_{OH} = -50mA	5.5V	3.85	4.9		
	I_{OH} = -75mA	5.5V	3.85	4.57		
V_{OL}	I_{OL} = 50µA	4.5V		0.001	0.1	V
		5.5V		0.001	0.1	
	I_{OL} = 24mA	4.5V		0.16	0.5	
	I_{OL} = 24mA	5.5V		0.14	0.5	
	I_{OL} = 50mA	5.5V		0.3	1.65	
	I_{OL} = 75mA	5.5V		0.47	1.65	
I_I	V_I = 5.5V or GND	0V to 5.5V		±0.008	±1	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	5.5V		0.1	20	µA
ΔI_{CC}	V_I = V_{CC} – 2.1V; Any Input	4.5V to 5.5V		0.1	1.5	mA
C_I	V_I = V_{CC} or GND	5V		2		pF
C_{PD}	C_L = 50pF, F = 1MHz	5V		63		pF

5.6 Switching Characteristics

C_L = 50 pF; over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	-40°C to 125°C			UNIT
				MIN	TYP	MAX	
t_{PLH}	D	Y	5V	3.9	4.6	15.5	ns
t_{PHL}			5V	3.9	5.6	15.5	ns
t_{PLH}	D	W	5V	3.9	5.5	16.9	ns
t_{PHL}			5V	3.8	4.4	16.9	ns
t_{PLH}	A, B, or C	Y	5V	4	4.7	20.2	ns
t_{PHL}			5V	4.9	7.1	20.2	ns
t_{PLH}	A, B, or C	W	5V	4.9	7	21.6	ns
t_{PHL}			5V	3.9	4.6	21.6	ns
t_{PLH}	$\overline{G}$	Y	5V	3	7	12.1	ns
t_{PHL}			5V	3	4.7	12.1	ns
t_{PLH}	$\overline{G}$	W	5V	3.4	4.7	13.5	ns
t_{PHL}			5V	3.4	6.9	13.5	ns

C_L = 50 pF; over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC}	-40°C to 125°C			UNIT
				MIN	TYP	MAX	
t_r		Any W or Y	5V	2	3.4	4.8	ns
t_f			5V	2.2	3.2	4.4	ns

5.7 Typical Characteristics

T_A = 25°C (unless otherwise noted)

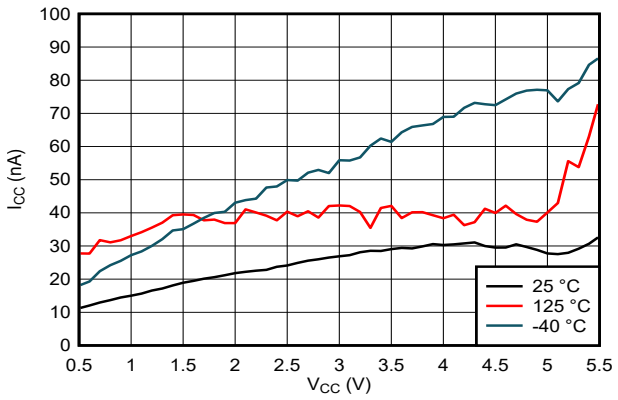


Figure 5-1. Supply Current Across Supply Voltage

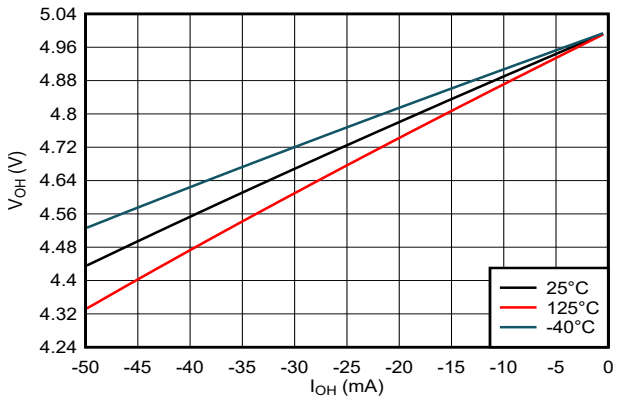


Figure 5-2. Output Voltage vs Current in HIGH State; 5V Supply

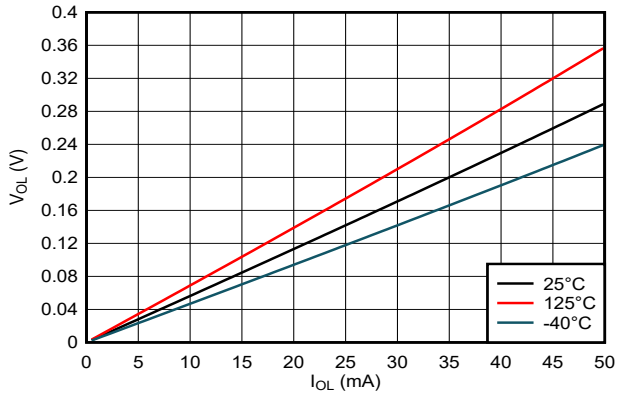
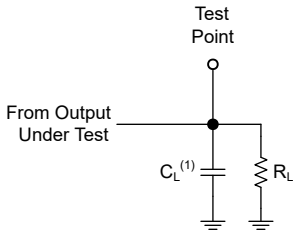


Figure 5-3. Output Voltage vs Current in LOW State; 5V Supply

6 Parameter Measurement Information

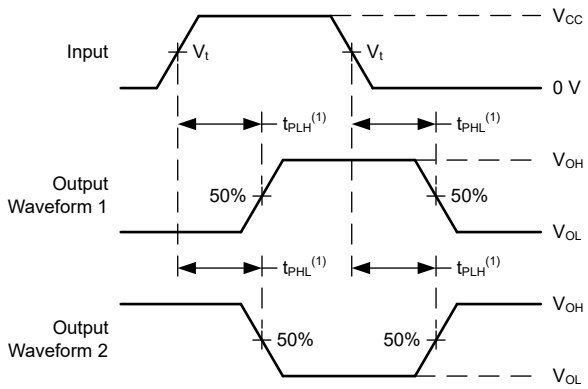
Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1MHz, Z_O = 50Ω, t_t < 2.5ns, V_t = 1.5V. For push-pull outputs, R_L = 500Ω.

The outputs are measured individually with one input transition per measurement.



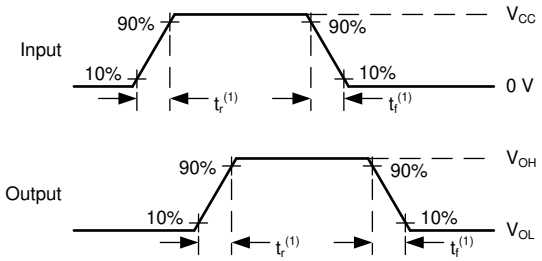
(1) C_L includes probe and test-fixture capacitance.

Figure 6-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

Figure 6-2. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t.

Figure 6-3. Voltage Waveforms, Input and Output Transition Times

7 Detailed Description

7.1 Overview

The SN74ACT151-Q1 is a high speed silicon gate CMOS multiplexer well suited to multiplexing and data routing applications. It contains a single 8:1 multiplexer.

The SN74ACT151-Q1 operates asynchronously, with the Y output being equal to the input selected by the address inputs (A, B, C). The W output is always the inverse of the Y output.

The strobe ($\overline{G}$) input forces the Y output low, and the W output high, regardless of the state of other inputs.

7.2 Functional Block Diagram

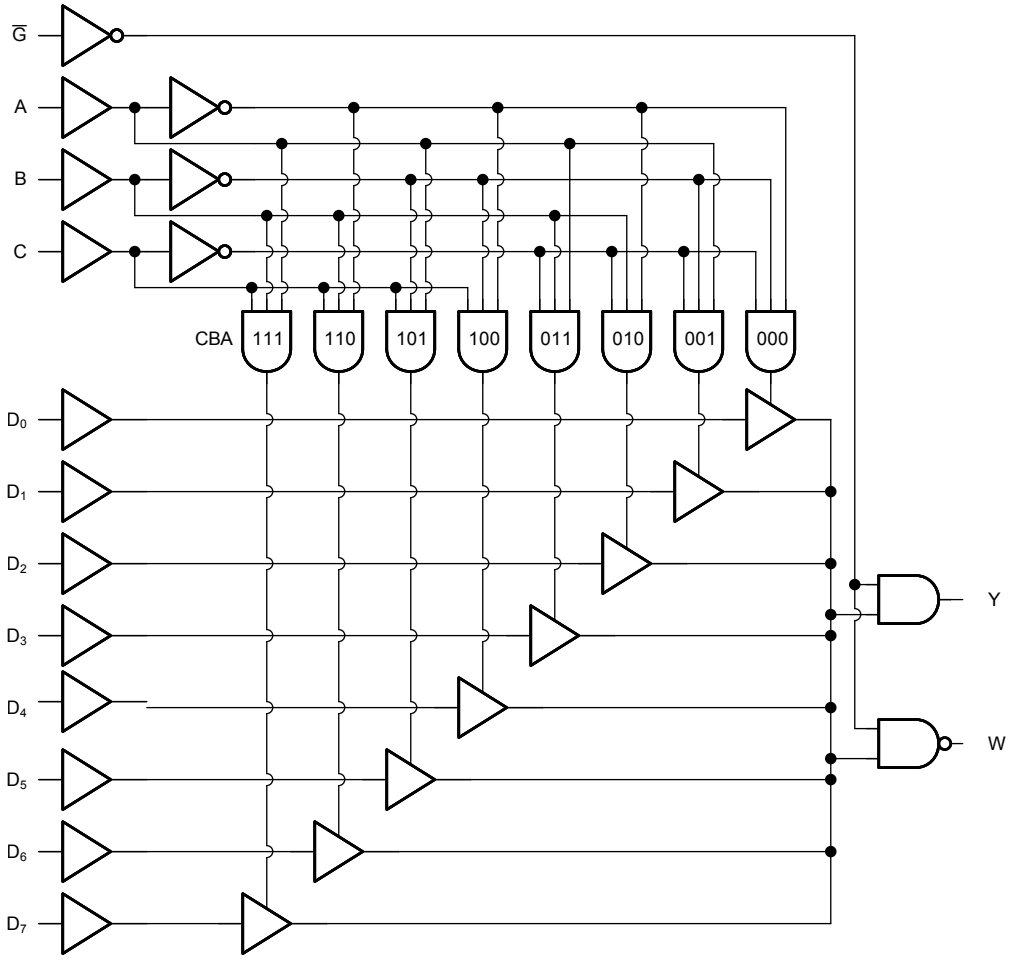


Figure 7-1. Logic Diagram (Positive Logic) for SN74ACT151-Q1

7.3 Feature Description

7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important to limit the output power of the device to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs must be left disconnected.

7.3.2 TTL-Compatible CMOS Inputs

This device includes TTL-compatible CMOS inputs. These inputs are specifically designed to interface with TTL logic devices by having a reduced input voltage threshold.

TTL-compatible CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

TTL-compatible CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the *Implications of Slow or Floating CMOS Inputs* application report.

Do not leave TTL-compatible CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10kΩ resistor is recommended and typically will meet all requirements.

7.3.3 Wettable Flanks

This device includes wettable flanks for at least one package. See the *Features* section on the front page of the data sheet where packages include this feature.

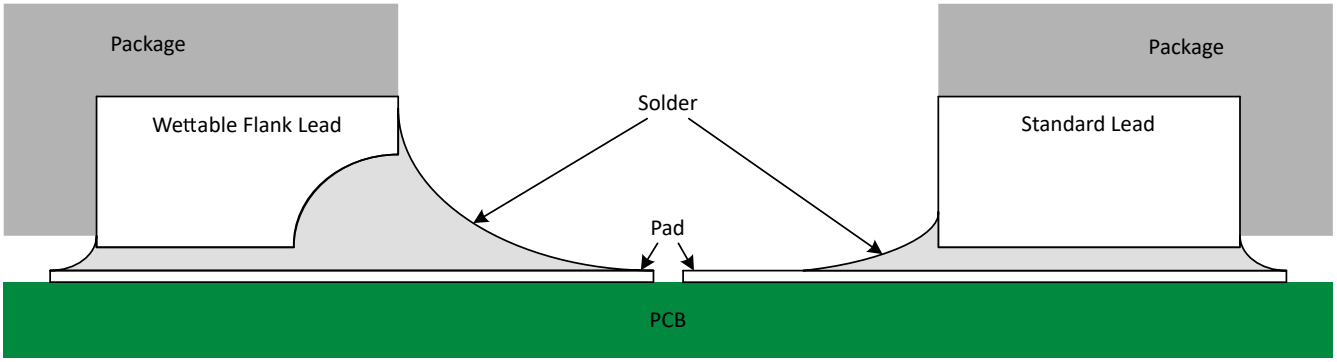


Figure 7-2. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering

Wettable flanks help improve side wetting after soldering, which makes QFN packages easier to inspect with automatic optical inspection (AOI). As shown in Figure 7-2, a wettable flank can be dimpled or step-cut to provide additional surface area for solder adhesion which assists in reliably creating a side fillet. See the mechanical drawing for additional details.

7.3.4 Clamp Diode Structure

As shown in Figure 7-3, the inputs and outputs to this device have both positive and negative clamping diodes.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

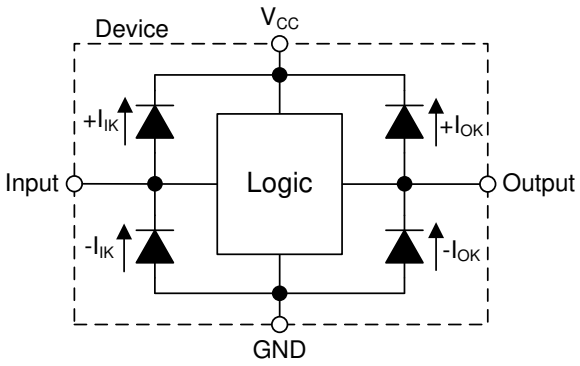


Figure 7-3. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Function Table lists the functional modes of the SN74ACT151-Q1.

Table 7-1. Function Table

INPUTS[1]				OUTPUTS[2]	
SELECT			STROBE	Y	W
C	B	A	$\overline{G}$		
X	X	X	H	L	H
L	L	L	L	D0	$\overline{D0}$
L	L	H	L	D1	$\overline{D1}$
L	H	L	L	D2	$\overline{D2}$
L	H	H	L	D3	$\overline{D3}$
H	L	L	L	D4	$\overline{D4}$
H	L	H	L	D5	$\overline{D5}$
H	H	L	L	D6	$\overline{D6}$
H	H	H	L	D7	$\overline{D7}$

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
(2) H = Driving High, L = Driving Low, Dx = Driving same value as Dx input, $\overline{Dx}$ = Driving inverted value from Dx input

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74ACT151-Q1 is an 8-to-1 data selector/multiplexer. This application shows an example of using the device with all required connections.

8.2 Typical Application

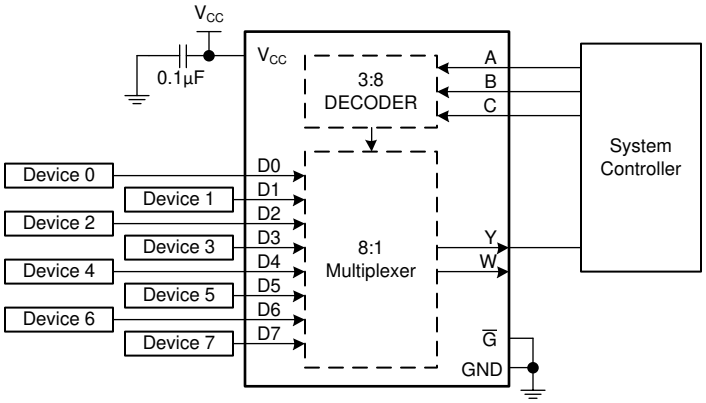


Figure 8-1. Typical Application Block Diagram

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74ACT151-Q1 plus the maximum static supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Ensure the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74ACT151-Q1 plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74ACT151-Q1 can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN74ACT151-Q1 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL}. When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices*.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74ACT151-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10kΩ resistor value is often used due to these factors.

The SN74ACT151-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74ACT151-Q1 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than (V_{CC} / $I_{O(max)}$)Ω. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in MΩ; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

8.2.3 Application Curve

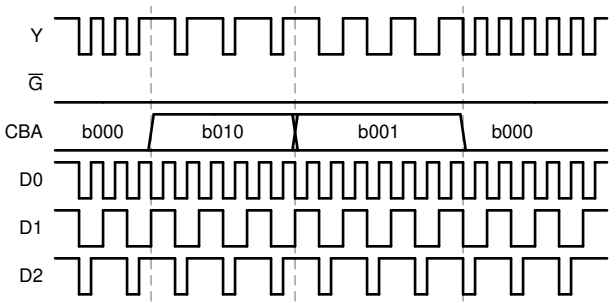


Figure 8-2. Application Timing Diagram

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1µF and 1µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

- Bypass capacitor placement
  - Place near the positive supply terminal of the device
  - Provide an electrically short ground return path
  - Use wide traces to minimize impedance
  - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
  - 8mil to 12mil trace width
  - Lengths less than 12cm to minimize transmission line effects
  - Avoid 90° corners for signal traces
  - Use an unbroken ground plane below signal traces
  - Flood fill areas around signal traces with ground
  - Parallel traces must be separated by at least 3x dielectric thickness
  - For traces longer than 12cm
    - Use impedance controlled traces
    - Source-terminate using a series damping resistor near the output
    - Avoid branches; buffer each signal that must branch separately

8.4.2 Layout Example

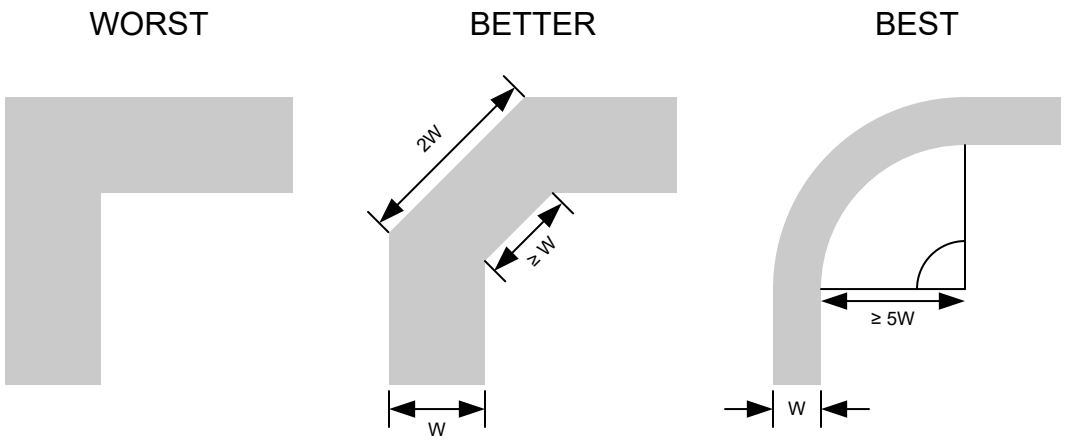


Figure 8-3. Example Trace Corners for Improved Signal Integrity

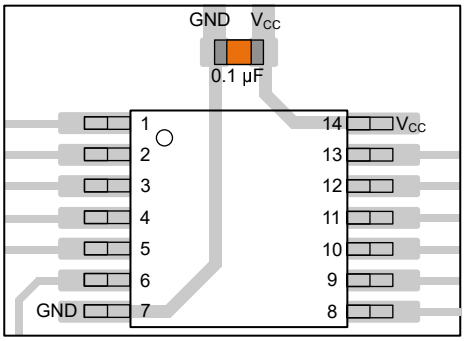


Figure 8-4. Example Bypass Capacitor Placement for TSSOP and Similar Packages

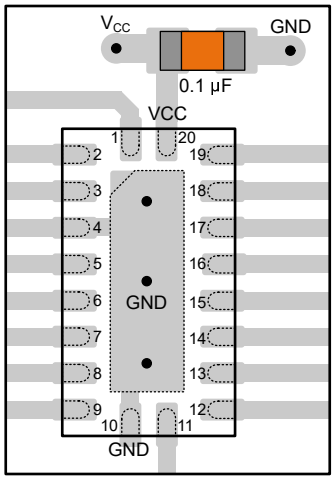


Figure 8-5. Example Bypass Capacitor Placement for WQFN and Similar Packages

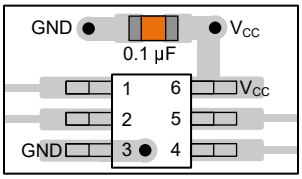


Figure 8-6. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages

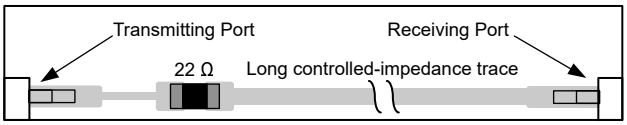


Figure 8-7. Example Damping Resistor Placement for Improved Signal Integrity

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *CMOS Power Consumption and C_{pd} Calculation* application report
- Texas Instruments, *Designing With Logic* application report
- Texas Instruments, *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices* application report

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.4 Trademarks

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9.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
May 2025	*	Initial Release

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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